

# N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD16410Q5A

特力材料886-3-5753170

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### **FEATURES**

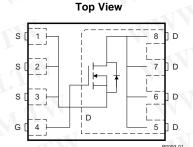
- Ultra Low Qg and Qgd
- Low Thermal Resistance
- Avalanche Rated
- · Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5mm x 6mm Plastic Package

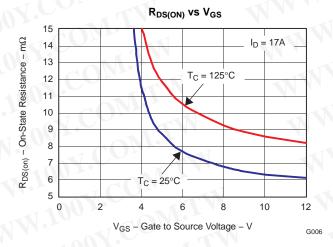
### **APPLICATIONS**

- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- Optimized for Control FET Applications

#### DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.





#### 胜特力电子(た海) 86-21-34970699 胜特力电子(深圳) 86-755-83298787 PRODUCT SUMMARY

V <sub>DS</sub>	Drain to Source Voltage	25		V
$Q_g$	Gate Charge Total (4.5V)	3.9		nC
$Q_{gd}$	Gate Charge Gate to Drain	1.1		nC
D	Drain to Course On Registeres	$V_{GS} = 4.5V$	9.6	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	V <sub>GS</sub> = 10V	6.8	mΩ
V <sub>GS(th)</sub>	Threshold Voltage	1.9		V

#### ORDERING INFORMATION

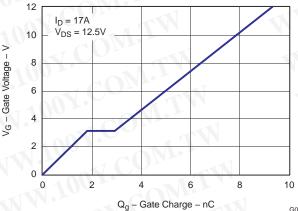
Device	Package	Media	Qty	Ship
CSD16410Q5A	SON 5X6 Plastic Package	13-inch reel	2500	Tape and Reel

### **ABSOLUTE MAXIMUM RATINGS**

$T_A = 2$	5°C unless otherwise stated	VALUE	UNIT
V <sub>DS</sub>	Drain to Source Voltage	25	V
V <sub>GS</sub>	Gate to Source Voltage	+16 / -12	V
	Continuous Drain Current, T <sub>C</sub> = 25°C	59	Α
I <sub>D</sub>	Continuous Drain Current <sup>(1)</sup>	16	Α
I <sub>DM</sub>	Pulsed Drain Current, T <sub>A</sub> = 25°C <sup>(2)</sup>	158	A
P <sub>D</sub>	Power Dissipation <sup>(1)</sup>	3	W
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C
E <sub>AS</sub>	Avalanche Energy, single pulse $I_D = 32A$ , $L = 0.1 mH$ , $R_G = 25\Omega$	51	mJ

- (1)  $R_{\theta,JA} = 42^{\circ}\text{C/W}$  on  $1\text{in}^2$  Cu (2 oz.) on 0.060" thick FR4 PCB.
- (2) Pulse width ≤300µs, duty cycle ≤2%

# Gate Charge



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### **ELECTRICAL CHARACTERISTICS**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

	PARAMETER	TEST CONDITIONS	MIN TYP MA	X UNIT
Static Cl	haracteristics	11111	100 1	
BV <sub>DSS</sub>	Drain to Source Voltage	$V_{GS} = 0V, I_{D} = 250\mu A$	25	V
I <sub>DSS</sub>	Drain to Source Leakage Current	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 20V	11007	1 μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +16/-12V$	10	00 nA
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.6 1.9 2	.3 V
D	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 17A$	9.6	12 mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = 10V, I_D = 17A$	6.8	.5 mΩ
9 <sub>fs</sub>	Transconductance	$V_{DS} = 15V, I_{D} = 17A$	38	S
Dynamic	Characteristics	N. Comment		
C <sub>ISS</sub>	Input Capacitance		570 74	10 pF
Coss	Output Capacitance	$V_{GS} = 0V$ , $V_{DS} = 12.5V$ , $f = 1MHz$	460 60	00 pF
C <sub>RSS</sub>	Reverse Transfer Capacitance		40	52 pF
$R_g$	Series Gate Resistance	AT CULT	0.7 1	.4 Ω
$Q_g$	Gate Charge Total (4.5V)	100,7	3.9	5 nC
$Q_{gd}$	Gate Charge Gate to Drain	V - 12 5V V 17A	1.1	nC
Q <sub>gs</sub>	Gate Charge Gate to Source	$V_{DS} = 12.5V, I_{D} = 17A$	1.8	nC
Qg(th)	Gate Charge at Vth	N. TO ONT.	1.1	nC
Q <sub>OSS</sub>	Output Charge	$V_{DS} = 13V$ , $V_{GS} = 0V$	10	nC
t <sub>d(on)</sub>	Turn On Delay Time	M. Tr.	6.2	ns
t <sub>r</sub>	Rise Time	$V_{DS} = 12.5V, V_{GS} = 4.5V, I_D = 17A$	10.7	ns
t <sub>d(off)</sub>	Turn Off Delay Time	$R_G = 2\Omega$	6.5	ns
t <sub>f</sub>	Fall Time	T'	3.6	ns
Diode C	haracteristics	TIN Inc. COM.		
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> = 17A, V <sub>GS</sub> = 0V	0.85	1 V
Q <sub>rr</sub>	Reverse Recovery Charge	$V_{DD} = 13V$ , $I_F = 17A$ , $di/dt = 300A/\mu s$	14	nC
t <sub>rr</sub>	Reverse Recovery Time	$V_{DD} = 13V$ , $I_F = 17A$ , $di/dt = 300A/\mu s$	18.2	ns

### THERMAL CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise stated)

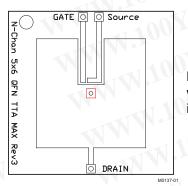
	PARAMETER	MIN TYP	MAX	UNIT
R <sub>θJC</sub>	Thermal Resistance Junction to Case <sup>(1)</sup>		3.8	°C/W
R <sub>θJA</sub>	Thermal Resistance Junction to Ambient <sup>(1)</sup> (2)		52	°C/W

<sup>(1)</sup> R<sub>0JC</sub> is determined with the device mounted on a 1 inch square 2 oz. Cu pad on a 1.5 x 1.5 in 0.060 inch thick FR4 board. R<sub>0JC</sub> is specified by design while  $R_{\theta JA}$  is determined by the user's board design. Device mounted on FR4 Material with 1 inch² of 2 oz. Cu.

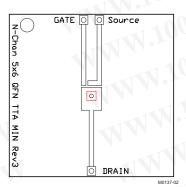
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Max  $R_{\theta JA} = 52^{\circ}C/W$  when mounted on 1 inch<sup>2</sup> of 2 oz. Cu.



Max  $R_{\theta JA} = 121^{\circ}C/W$  when mounted on minimum pad area of 2 oz. Cu.

### TYPICAL MOSFET CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise stated)

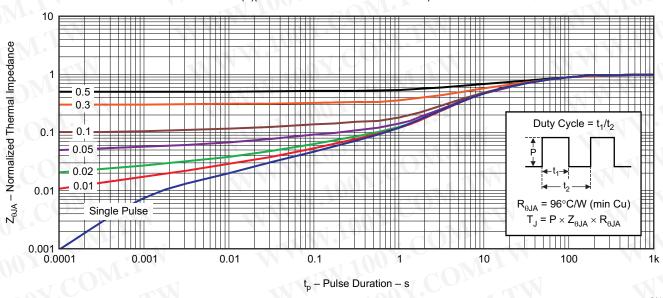


Figure 1. Transient Thermal Impedance

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# **TYPICAL MOSFET CHARACTERISTICS (continued)**

(T<sub>A</sub> = 25°C unless otherwise stated)

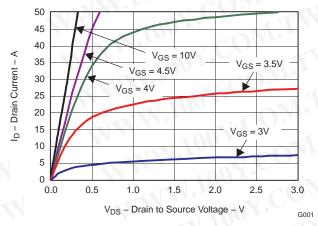


Figure 2. Saturation Characteristics

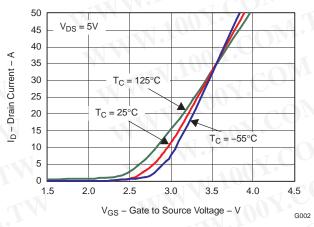


Figure 3. Transfer Characteristics

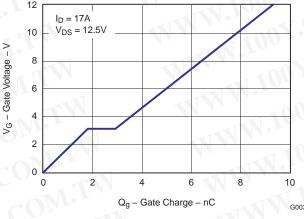


Figure 4. Gate Charge

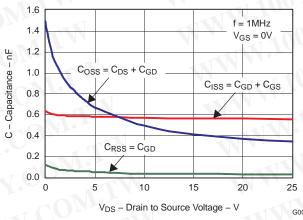


Figure 5. Capacitance

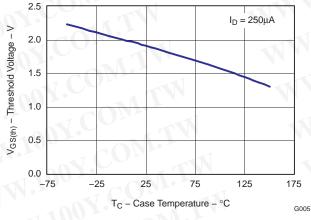


Figure 6. Threshold Voltage vs. Temperature

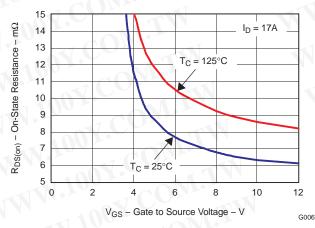


Figure 7. On Resistance vs. Gate Voltage



### TYPICAL MOSFET CHARACTERISTICS (continued)

(T<sub>A</sub> = 25°C unless otherwise stated)

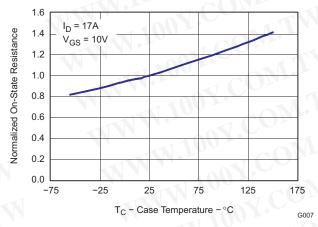


Figure 8. On Resistance vs. Temperature

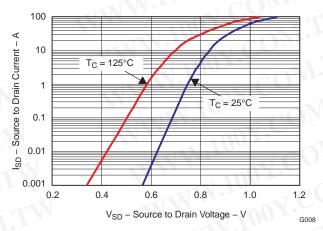


Figure 9. Typical Diode Forward Voltage

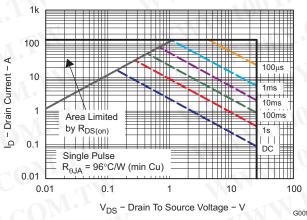


Figure 10. Maximum Safe Operating Area

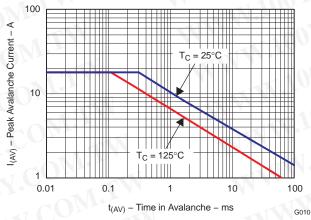


Figure 11. Single Pulse Unclamped Inductive Switching

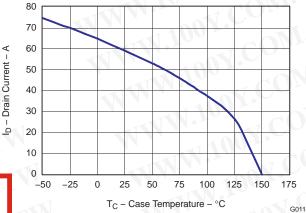
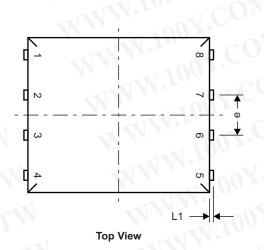


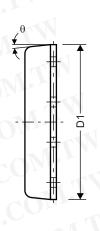
Figure 12. Maximum Drain Current vs. Temperature



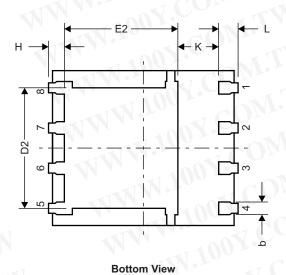
## **MECHANICAL DATA**

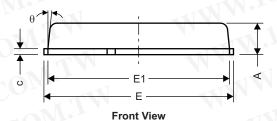
## **Q5A Package Dimensions**





Side View



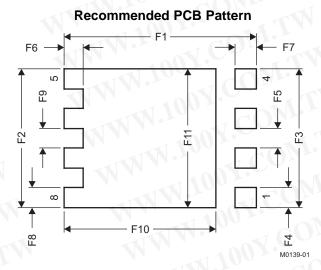


DIM		MILLIMETERS	- <b>x</b> 1
	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.33	0.41	0.51
С	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
е		1.27 BSC	
Н	0.41	0.51	0.61
K	1.10	- 1 1 NU 1.	
CONE	0.51	0.61	0.71
L1	0.06	0.13	0.20
θ	0°		12°

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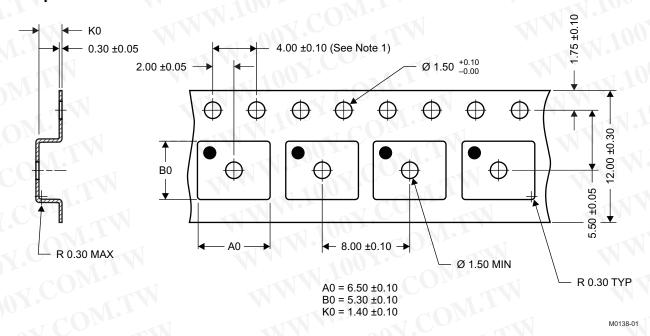




DIM	MILLIN	IETERS	INC	HES
DIN	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.46	4.56	0.176	0.18
F3	4.46	4.56	0.176	0.18
F4	0.65	0.7	0.026	0.028
F5	0.62	0.67	0.024	0.026
F6	0.63	0.68	0.025	0.027
F7	0.7	0.8	0.028	0.031
F8	0.65	0.7	0.026	0.028
F9	0.62	0.67	0.024	0.026
F10	4.9	5	0.193	0.197
F11	4.46	4.56	0.176	0.18

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

### **Q5A Tape and Reel Information**



#### Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible



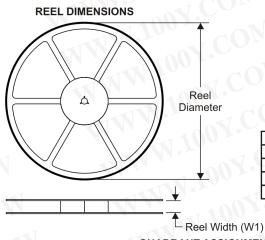
### **REVISION HISTORY**

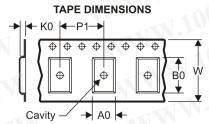
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•	Deleted the Package Marking Information section	1007	

# PACKAGE MATERIALS INFORMATION

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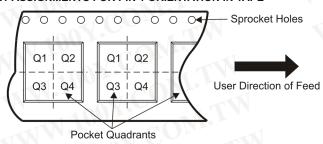
### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

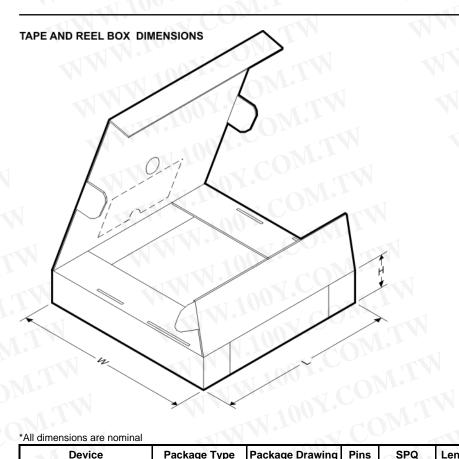


#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16410Q5A	SON	DQJ	8	2500	330.2	12.4	6.5	5.3	1.4	8.0	12.0	Q1

# PACKAGE MATERIALS INFORMATION

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# \*All dimensions are nominal

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In								
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dimensions are nominal		Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	00Y.C

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